

UNITED STATES PATENT AND TRADEMARK OFFICE  
**CERTIFICATE OF CORRECTION**

PATENT NO. : 7,212,556 B1  
APPLICATION NO. : 09/504782  
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INVENTOR(S) : Masahiro Kume et al.

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It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

claim 1, column 23, line 24, “In<sub>x</sub>Ga<sub>1-x</sub>N” should read “In<sub>y</sub>Ga<sub>1-y</sub>N.”

claim 8, column 24, line 24, “In<sub>x</sub>Ga<sub>1-x</sub>N” should read “In<sub>y</sub>Ga<sub>1-y</sub>N.”

claim 9, column 24, lines 27-29, “a contact layer, which is made of a nitride semiconductor of a first conductivity type and is formed over a substrate;” should be removed.

claim 9, column 24, line 32, “contact layer” should read “substrate”

claim 9, column 24, line 37, “over the active layer; and” should read “over the active layer;”

claim 9, column 24, between line 37 and 38, “an electrode formed over the second cladding layer; and” should be added.

claim 9, column 24, line 38, “the first conductivity type” should read “the second conductivity type”

claim 9, column 24, line 39, “the substrate and” should be removed.

claim 9, column 24, line 39, “the first cladding layer” should read “the second cladding layer.”

claim 9, column 24, line 39, after “the first cladding layer” add “and the electrode”

Signed and Sealed this  
Third Day of January, 2012



David J. Kappos  
Director of the United States Patent and Trademark Office